

Description

The RS1G120MNTB uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

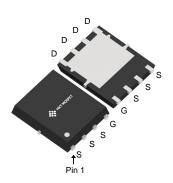
 $V_{DS} = 40V I_D = 40A$ $R_{DS(ON)} < 14m\Omega V_{GS} = 10V$

Application

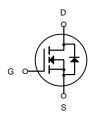
Battery protection

Load switch

Uninterruptible power supply



DFN5X6-8L



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
RS1G120MNTB	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units		
VDS	Drain-Source Voltage	ain-Source Voltage 40			
Vgs	Gate-Source Voltage	±20	V		
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ 10V ¹	40	А		
I _D @T _C =100°C	Continuous Drain Current, Vos @ 10V1	28	Α		
Ірм	Pulsed Drain Current ²	160	Α		
EAS	Single Pulse Avalanche Energy ³	50	mJ		
Тѕтс	Storage Temperature Range	Range -55 to 175			
TJ	Operating Junction Temperature Range	-55 to 175	°C		



Electrical Characteristics (T_C=25 ℃ unless otherwise noted)

Parameter	Parameter Symbol		Min	Тур	Max	Unit	
Off Characteristics	·		•				
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA 40		-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)						1	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1	1.6	2.5	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	11	14	mΩ	
Forward Transconductance	g Fs	V _{DS} =5V,I _D =20A	30	-	-	S	
Dynamic Characteristics (Note4)						1	
Input Capacitance	C _{lss}	051414 014	-	1540	-	PF	
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$	-	171	-	PF	
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	115	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	5.0	-	nS	
Turn-on Rise Time	t _r	$V_{DD}=20V, I_{D}=20A, R=1\Omega$	-	24	-	nS	
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =3 Ω	-	38	-	nS	
Turn-Off Fall Time	t _f		-	12	-	nS	
Total Gate Charge	Qg	\/ 00\/ L 00A	-	24	-	nC	
Gate-Source Charge	Q _{gs}	$V_{DS}=30V,I_{D}=30A,$	-	5.9	-	nC	
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	3.6	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =30A	-	-	1.2	V	
Diode Forward Current (Note 2)	Is		-	-	48	А	
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =30A	-	9		nS	
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	15		nC	
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)					

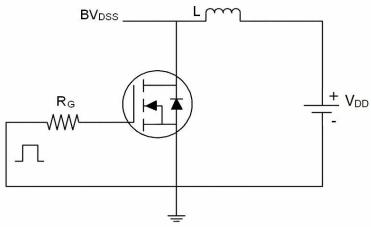
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** E_{AS} condition: $Tj=25^{\circ}C$, $V_{DD}=30V$, $V_{G}=10V$,L=0.5mH, $Rg=25\Omega$

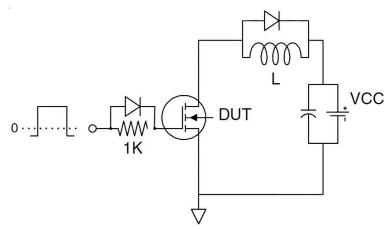


Test circuit

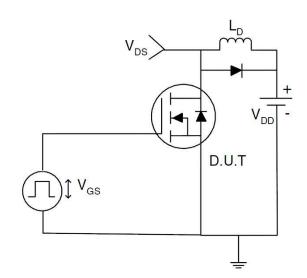
1) E_{AS} test Circuits



2) Gate charge test Circuit

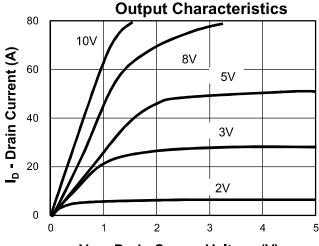


3) Switch Time Test Circuit

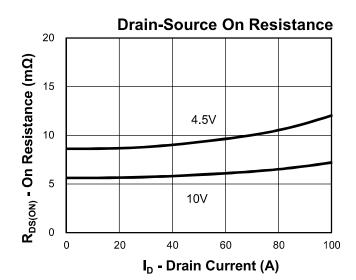


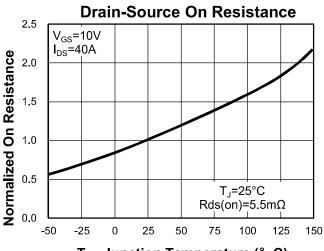


Typical Performance Characteristics

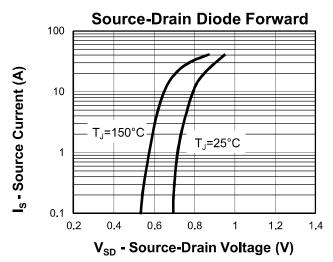


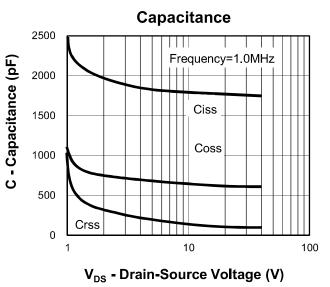


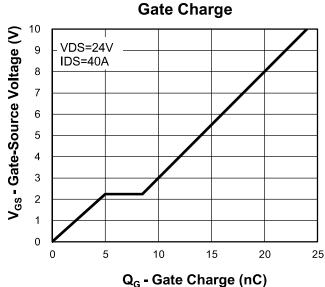




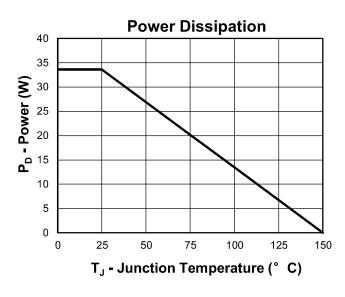
T_J - Junction Temperature (° C)

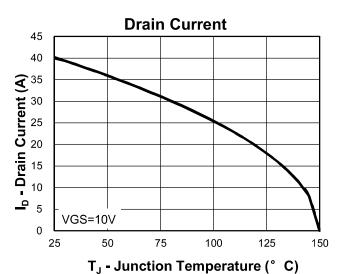


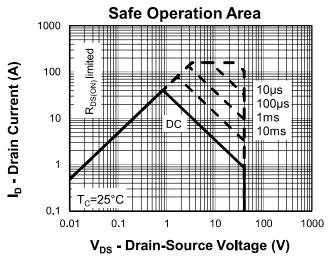


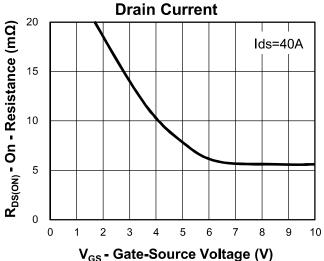




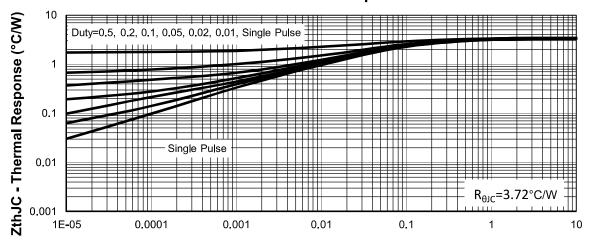








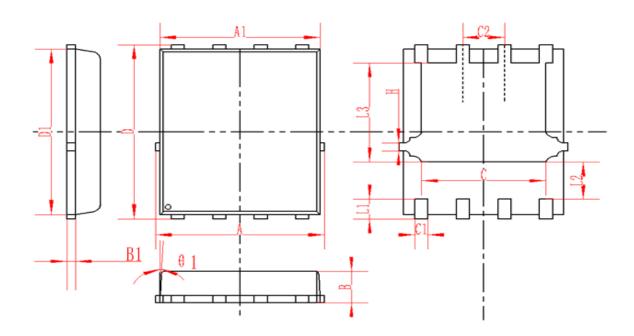
Thermal Transient Impedance



Square Wave Pulse Duration (sec)



DFN5X6-8L Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
А	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
В	0.9	0.95	1	0.035	0.037	0.039
B1		0.254REF			0.010REF	
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Η	0.24	0.25	0.26	0.009	0.010	0.010



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